

L Number	Hits	Search Text	DB	Time stamp
1	489	garnet.ab.	USPAT	2003/04/04 16:46
2	86	garnet.ab. and semiconductor	USPAT	2003/04/04 16:55
3	0	(garnet.ab. and semiconductor) and 'm.sub.3 al.sub.5. o.sub.12'	USPAT	2003/04/04 16:47
4	0	'm.sub.3 al.sub.5. o.sub.12'	USPAT	2003/04/04 16:47
5	0	'm.sub.3 al.sub.5 o.sub.12'	USPAT	2003/04/04 16:47
6	16	'Re.sub.3 al.sub.5 o.sub.12'	USPAT	2003/04/04 16:47
7	75	(garnet.ab. and semiconductor) and (coating or layer or film)	USPAT	2003/04/04 17:11
8	0	garnet.ab. and 'reactive chamber'	USPAT	2003/04/04 17:12
9	0	garnet.ab. and 'etch reactor'	USPAT	2003/04/04 17:12
10	0	garnet.ab. and 'turbine rotor'	USPAT	2003/04/04 17:13
11	15	garnet.ab. and halogen	USPAT	2003/04/04 17:20
12	7	garnet.ab. and (wafer with silicon)	USPAT	2003/04/04 17:22
13	4	Gobain and garnet	USPAT	2003/04/04 17:23
14	0	simpson.in. and garnet	USPAT	2003/04/04 17:24
15	0	billieres.in. and garnet	USPAT	2003/04/04 17:24
16	0	main.in. and garnet	USPAT	2003/04/04 17:24
17	0	drouin.in. and garnet	USPAT	2003/04/04 17:25
18	7	garnet.clm. and 'thermal spray'	USPAT	2003/04/04 17:29
19	255	garnet and semiconductor	EPO; JPO; DERWENT	2003/04/04 17:29
20	157	(garnet and semiconductor) and (film or coating or layer)	EPO; JPO; DERWENT	2003/04/04 17:30